編號:

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國立成功大學九十八學年度碩士班招生考試試題

共3頁,第1頁

系所組別: 光電科學與工程研究所

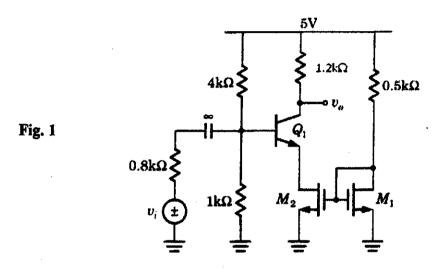
考試科目: 電子學

考試日期: 0307·節次:1

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1. For the ampilifer in the Fig. 1, let the parameters of transistors M1, M2 and Q1 $\mu_n C_{ox}$ =200 μ A/V², V₁=1V, (W/L)_{M1}=10, (W/L)_{M2}=20 and β (Q1)=499. Please find

- (a) Output DC voltage v_o (10%)
- (b) Small signal voltage gain v₀/v_i. (10%)



- 2. The differential amplifier circuit of Fig. 2 utilizes a resistor connected to the negative power supply to establish the bias current I. where Q_1 and Q_2 $\alpha \sim 1$
- (a) For $v_{B1}=v_{id}/2$ and $v_{B2}=-v_{id}/2$ where v_{id} is a small signal with zero average, find the magnitude of the differential gain, $|v_o/v_{id}|$ (5%)
- (b) For $v_{Bi} = v_{B2} = v_{icm}$, find the magnitude of the common-mode gain, $|v_o/v_{icm}|$. (5%)
- (c) Find the CMRR. (5%)

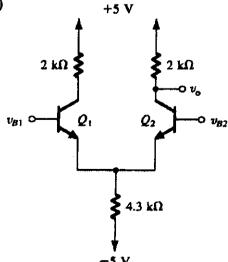


Fig. 2

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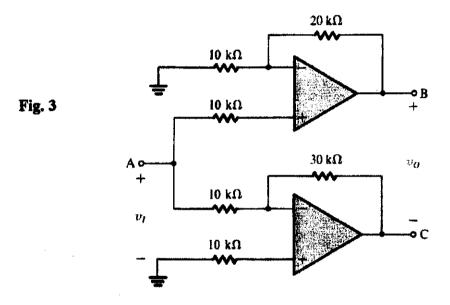
系所組別: 光電科學與工程研究所

考試科目: 電子學

考試日期:0307,節次:1

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- 3. The circuit shown in fig. 3 is intended to supply a voltage to floating loads while making greatest possible use of the available power supply.
- (a) Assuming ideal OP amps, sketch the voltage waveforms at nodes B and C for a
- 1-V peak-to-peak sine wave applied at node A. Also sketch the vo. (5%)
- (b) What is the voltage gain v_0/v_i . (5%)
- (c) Assuming that the OP amps operate from ±15-V power supplies and that their output saturates at ±14V. What is the largest sine wave output that can be accommodated? Specify both its peak to peak and rms values. (5%)



4. For the circuits in Fig. 4, $\mu_n C_{ox} = 2.5 \ \mu_p C_{ox} = 20 \ \mu\text{A/V}^2$, $|V_t| = 1\text{V}$, $\lambda = 0$, $\gamma = 0$, $L = 10 \ \mu\text{m}$, and $W = 30 \ \mu\text{m}$, unless otherwise specified. Find the labeled currents and voltages. (15%)

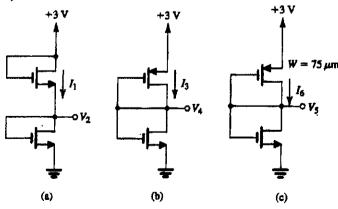


Fig. 4

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5. For a digital logic inverter fabricated in a 0.8- μ m CMOS technology for which k_n ' = 120 μ A/V², k_p ' = 60 μ A/V², $V_{tn} = |V_{tp}| = 0.7$ V, $V_{DD} = 3$ V, $L_n = L_p = 0.8$ μ m, $W_n = 1.2$ μ m, and $W_p = 2.4$ μ m, find:

- (a) the output resistance for $v_0 = V_{OL}$, and for $v_0 = V_{OH}$ (5%)
- (b) the maximum current that the inverter can sink or source while the output remains within 0.1 V of ground or V_{DD} , respectively (5%)
- (c) V_{IH} , V_{IL} , and noise margins NM_H , NM_L (5%)
- (d) the peak current drawn from the 3-V supply during switching (5%)
- 6. For the transistor shown in Fig. 5, assume $\alpha=1$ and $v_{BE}=0.5$ V at the edge of conduction. What are the values of V_E and V_D for $V_B=0$ V? For what value of V_B does the transistor cut off? Saturate? In each case, what values of V_E and V_C result? (15%)

